

RGW60NL65HRBTL

650V 30A Field Stop Trench IGBT

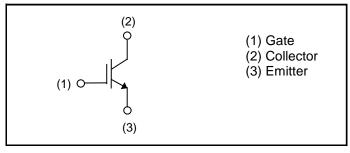
V _{CES}	650V
I _C	30A
V _{CE(sat) (Typ.)}	1.5V
P _D	187W

Outline LPDL (TO-263L) (1) (3)

Features

- 1) AEC-Q101 Qualified
- 2) Low Collector Emitter Saturation Voltage
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

●Inner Circuit



Application

Automotive

On & Off Board Chargers

DC-DC Converters

PFC

Industrial Inverter

Packaging Specifications

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	Packaging	Taping
	Reel Size (mm)	330
Type	Tape Width (mm)	24
Type	Basic Ordering Unit (pcs)	1,000
	Packing Code	TL
	Marking	RGW60NL65

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	67	Α
	T _C = 100°C	I _C	40	Α
Pulsed Collector Current		I _{CP} *1	120	Α
Power Dissipation	T _C = 25°C	P_{D}	187	W
	T _C = 100°C	P _D	93	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{jmax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raidilletei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.80	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol Conditions		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	ı	ı	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	ı	ı	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	ı	ı	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$V_{CE} = 5V, I_{C} = 20.0 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage		$I_C = 30A, V_{GE} = 15V,$				
	$V_{CE(sat)}$	$T_j = 25$ °C $T_i = 175$ °C	-	1.5	1.9	V
		T _j = 175°C	-	1.85	-	

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	$V_{CE} = 30V$,	-	2530	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$,	-	65	-	pF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	46	-	
Total Gate Charge	Q_g	V _{CE} = 400V,	-	84	-	
Gate - Emitter Charge	Q_ge	$I_{\rm C} = 30A,$	-	17	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	31	-	
Turn - on Delay Time	t _{d(on)}		-	34	-	
Rise Time	t _r	$I_C = 15A, V_{CC} = 400V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	9	-	ns
Turn - off Delay Time	t _{d(off)}	$T_i = 25^{\circ}C$	-	122	-	
Fall Time	t _f	Inductive Load	-	40	-	
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	0.18	-	
Turn - off Switching Loss	E _{off}		-	0.25	-	mJ
Turn - on Delay Time	t _{d(on)}		-	33	-	
Rise Time	t _r	I_{C} = 15A, V_{CC} = 400V, V_{GE} = 15V, R_{G} = 10 Ω , T_{j} = 175°C Inductive Load *E _{on} include diode reverse recovery	-	9	-	
Turn - off Delay Time	t _{d(off)}		-	133	-	ns
Fall Time	t _f		-	63	-	1
Turn - on Switching Loss	E _{on}		-	0.18	-	
Turn - off Switching Loss	E _{off}		-	0.31	-	mJ
Reverse Bias Safe Operating Area	RBSOA	$I_C = 120A$, $V_{CC} = 520V$, $V_P = 650V$, $V_{GE} = 15V$, $R_G = 100\Omega$, $T_j = 175^{\circ}C$	FU	LL SQUA	RE	-

Electrical Characteristic Curves

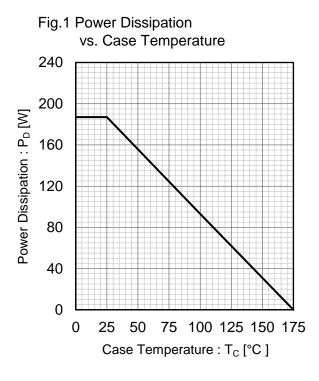


Fig.2 Collector Current vs. Case Temperature 90 80 70 Collector Current : I_C [A] 60 50 40 30 20 T_i ≤ 175°C 10 0 25 50 75 100 125 150 175 0 Case Temperature : T_C [°C]

Fig.3 Forward Bias Safe Operating Area

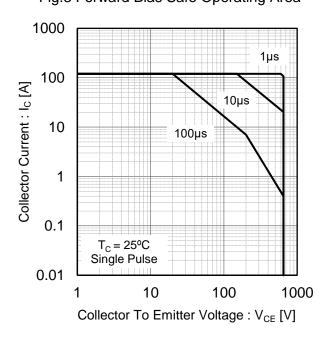
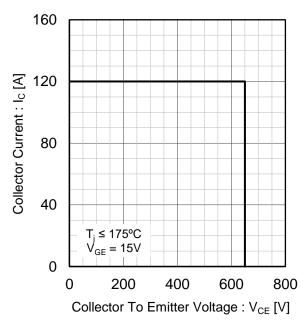


Fig.4 Reverse Bias Safe Operating Area



● Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

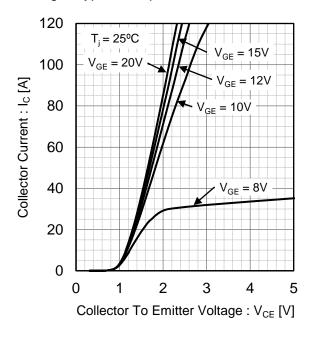


Fig.6 Typical Output Characteristics

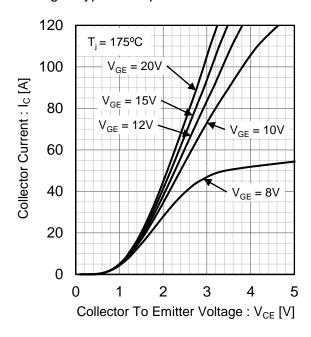


Fig.7 Typical Transfer Characteristics

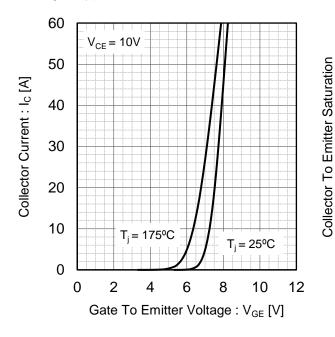
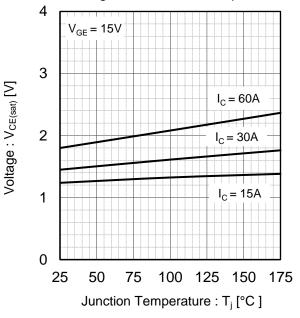


Fig.8 Typical Collector to Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation

● Electrical Characteristic Curves

Fig.9 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

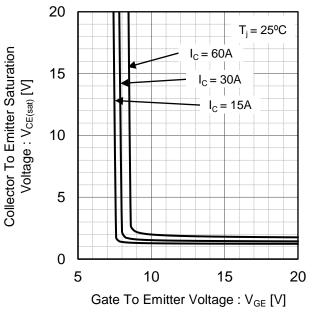


Fig.10 Typical Collector to Emitter Saturation Voltage vs. Gate to Emitter Voltage

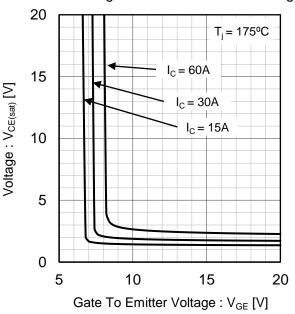


Fig.11 Typical Capacitance vs. Collector to Emitter Voltage

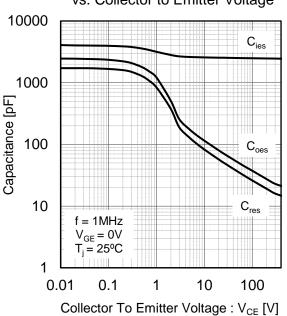
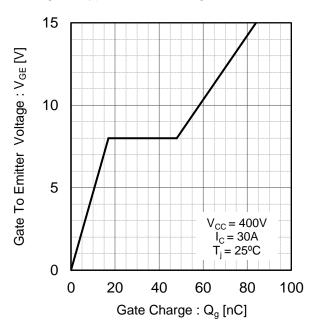
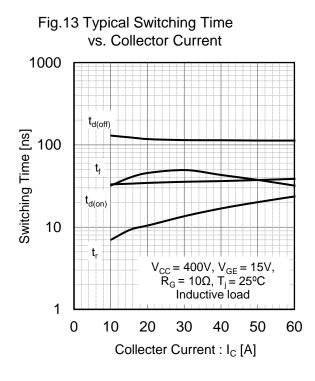


Fig.12 Typical Gate Charge



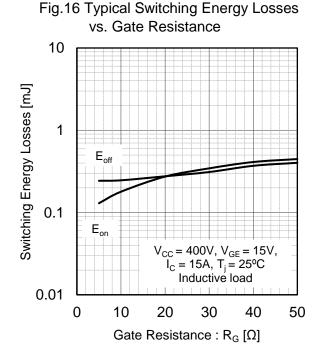
• Electrical Characteristic Curves



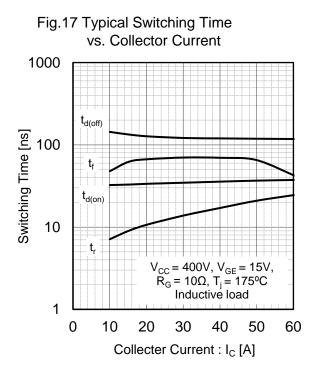
vs. Gate Resistance 1000 $t_{d(off)}$ Switching Time [ns] 100 t_{d(on)} 10 $I_{C} = 400V, V_{GE} = 15V,$ $I_{C} = 15A, T_{j} = 25^{\circ}C$ Inductive load 1 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Time

Fig.15 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 E_{on} $V_{CC} = 400V, V_{GE} = 15V,$ $R_{G} = 10\Omega, T_{j} = 25^{\circ}C$ Inductive load 0.01 0 10 20 30 40 50 60 Collecter Current : I_C [A]



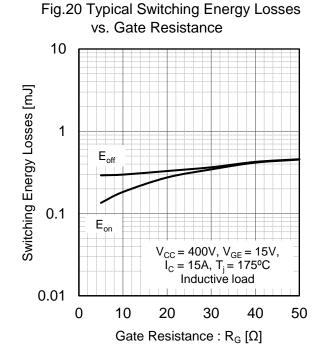
• Electrical Characteristic Curves



vs. Gate Resistance 1000 $t_{d(off)}$ Switching Time [ns] 100 $t_{d(on)}$ 10 $V_{CC} = 400V, V_{GE} = 15V,$ $I_{C} = 15A, T_{j} = 175^{\circ}C$ Inductive load 1 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

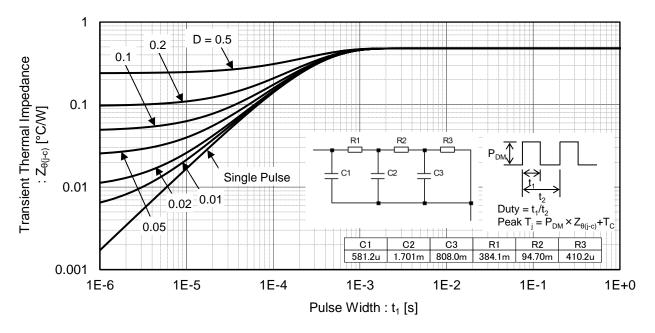
Fig.18 Typical Switching Time

Fig.19 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 E_{on} $V_{CC} = 400V, V_{GE} = 15V,$ $R_G = 10\Omega, T_j = 175^{\circ}C$ Inductivé load 0.01 0 10 20 30 40 50 60 Collecter Current : I_C [A]



•Electrical Characteristic Curves

Fig.21 Typical IGBT Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

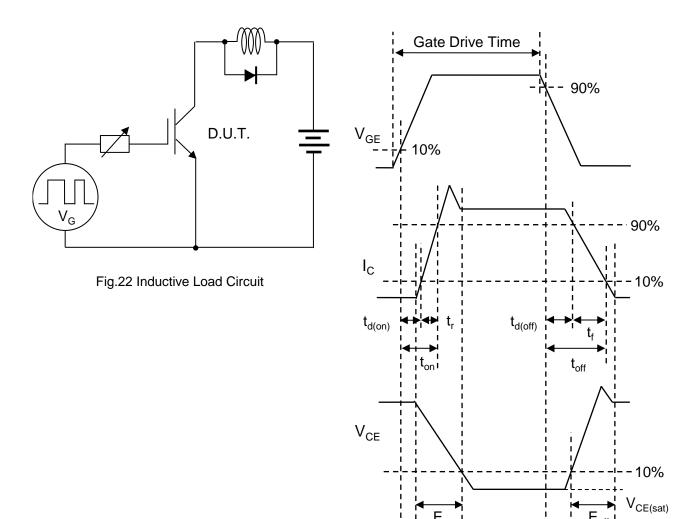


Fig.23 Inductive Load Waveform

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